

# Absolute Maximum Ratings (@TA = +25 °C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	-45	V
Collector-Emitter Voltage (Forward Blocking)	V <sub>CEO</sub>	-40	V
Emitter-collector voltage (Reverse Blocking)	V <sub>ECO</sub>	-3	V
Emitter-Base Voltage	V <sub>EBO</sub>	-7	V
Continuous Collector Current (Note 5)	Ic	-1.5	Α
Base Current	I <sub>B</sub>	-500	mA
Peak Pulse Current	I <sub>CM</sub>	-5	Α

## Thermal Characteristics (@ $T_A = +25$ °C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
Power Dissipation	(Note 5)	В	310	mW	
rowei Dissipation	(Note 6)	P <sub>D</sub>	350		
They weed Desistance Investigate Austriant	(Note 5)	Б	403	°C/W	
Thermal Resistance, Junction to Ambient	(Note 6)	$R_{\theta JA}$	357	G/VV	
Thermal Resistance, Junction to Leads	(Note 7)	$R_{ heta JL}$	350	°C/W	
Operating and Storage Temperature Range		$T_{J}, T_{STG}$	-55 to +150	∞	

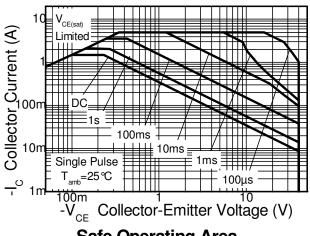
# ESD Ratings (Note 8)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

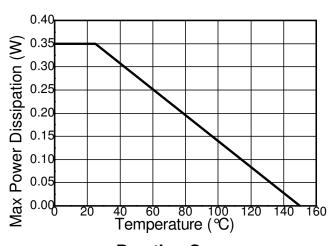
- 5. For a device mounted on minimum recommended pad layout 1oz copper that is on a single-sided FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.
- 6. Same as Note 5, except the device is mounted on 15 mm x 15mm 1oz copper.
  7. Thermal resistance from junction to solder-point (at the end of the leads).
  8. Refer to JEDEC specification JESD22-A114 and JESD22-A115.



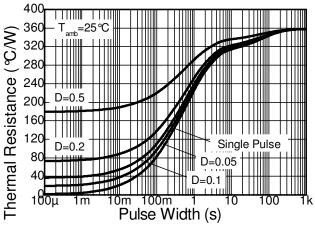
### **Thermal Characteristics and Derating Information**



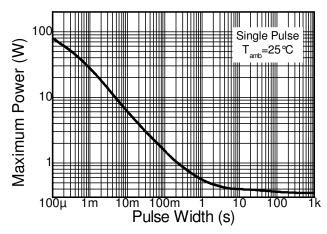
**Safe Operating Area** 



**Derating Curve** 



**Transient Thermal Impedance** 



**Pulse Power Dissipation** 





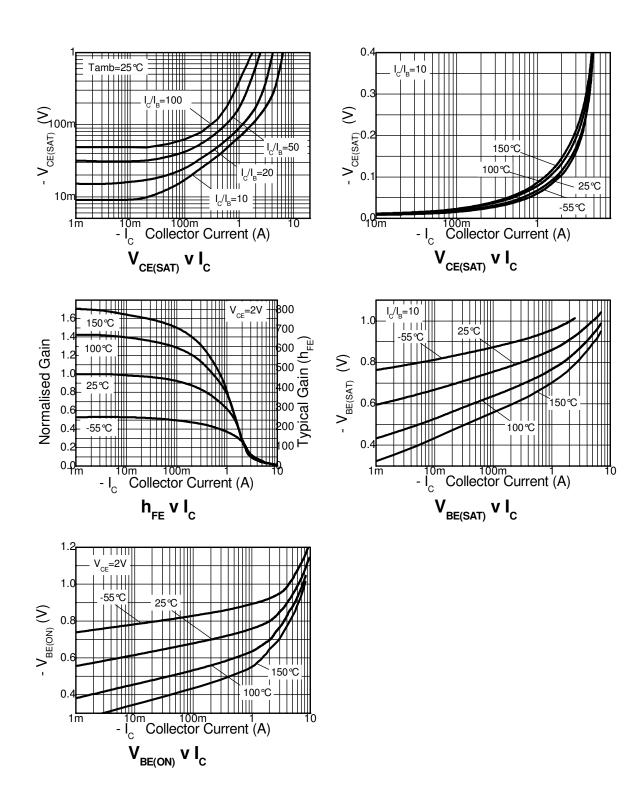
## Electrical Characteristics (@T<sub>A</sub> = +25 °C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	$BV_CBO$	-45	-75	-	V	$I_{C} = -100 \mu A$
Collector-Emitter Breakdown Voltage (Note 9)	$BV_CEO$	-40	-65	-	V	I <sub>C</sub> = -10mA
Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	-7	-8.2	-	V	$I_E = -100 \mu A$
Emitter-Base Breakdown Voltage	BV <sub>ECO</sub>	-3	-8.7	-	V	$I_E = -100 \mu A$
Collector-Base Cutoff Current	I <sub>CBO</sub>	-	< -1	-50	nA	V <sub>CB</sub> = -36V
Collector-base Cuton Current		-	1	-20	μΑ	V <sub>CB</sub> = -36V, T <sub>amb</sub> = +100 ℃
Emitter-Base Cutoff Current	I <sub>EBO</sub>	-	< -1	-50	nA	V <sub>EB</sub> = -5.6V
		300	450	900		$I_C = -10 \text{mA}, V_{CE} = -2 \text{V}$
Static Forward Current Transfer Ratio (Note 9)	hee	120	200	-	_	$I_C = -1.5A, V_{CE} = -2V$
Static Forward Guitent Transfer Fratio (Note 9)	h <sub>FE</sub>	15	40	-	-	I <sub>C</sub> = -3A, V <sub>CE</sub> = -2V
	V <sub>CE(sat)</sub>	-	-75	-95	mV	$I_C = -0.5A$ , $I_B = -20mA$
			-200	-290		$I_C = -1A, I_B = -20mA$
Collector-Emitter Saturation Voltage (Note 9)		-	-95	-115		$I_C = -1A$ , $I_B = -100mA$
		-	-160	-190		$I_C = -1.5A$ , $I_B = -75mA$
		-	-245	-300		$I_C = -3A$ , $I_B = -300mA$
Base-Emitter Saturation Voltage (Note 9)	$V_{BE(sat)}$	-	-915	-1000	mV	$I_C = -1.5A$ , $I_B = -75mA$
Base-Emitter Saturation Voltage (Note 9)	$V_{BE(on)}$	-	-825	-900	mV	$I_C = -1.5A$ , $V_{CE} = -2V$
Output Capacitance	$C_{obo}$	-	17.4	25	pF	$V_{CB} = -10V$ , $f = 1MHz$
Transition Frequency	f <sub>T</sub>	-	270	-	MHz	$V_{CE} = -10V, I_{C} = -50mA,$ f = 50MHz
Delay Time	t <sub>(d)</sub>	-	34	-	ns	
Rise Time	t <sub>(r)</sub>	-	41	-	ns	$V_{CC} = -15V, I_{C} = -750mA,$
Storage Time	t <sub>(s)</sub>	-	266	-	ns	$I_{B1} = -I_{B2} = -15mA$
Fall Time	$t_{(f)}$	-	53	-	ns	

Notes: 9. Measured under pulsed conditions. Pulse width  $\leq$  300  $\mu$ s. Duty cycle  $\leq$  2%.



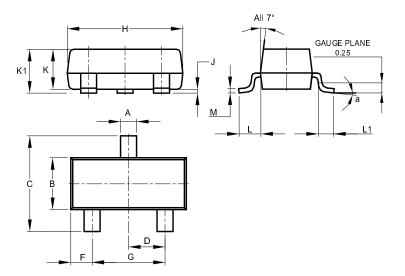
### Typical Electrical Characteristics (@T<sub>A</sub> = +25 ℃, unless otherwise specified.)





## **Package Outline Dimensions**

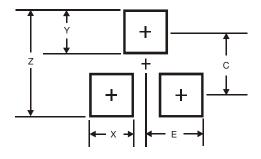
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



SOT23					
Dim	Min	Max	Тур		
Α	0.37	0.51	0.40		
В	1.20	1.40	1.30		
С	2.30	2.50	2.40		
D	0.89	1.03	0.915		
F	0.45	0.60	0.535		
G	1.78	2.05	1.83		
Н	2.80	3.00	2.90		
J	0.013	0.10	0.05		
K	0.890	1.00	0.975		
K1	0.903	1.10	1.025		
L	0.45	0.61	0.55		
L1	0.25	0.55	0.40		
М	0.085	0.150	0.110		
а	8°				
All Dimensions in mm					

## **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Z	2.9
Х	0.8
Υ	0.9
С	2.0
E	1.35





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